

Application Data Sheet

Application Information

Application Type:: Regular
Subject Matter:: Utility
Suggested Group Art Unit:: N/A
CD-ROM or CD-R?:: None
Sequence submission?:: None
Computer Readable Form (CRF)?:: No
Title:: ATOMIC LAYER DEPOSITION OF
TITANIUM NITRIDE USING BATCH TYPE
CHAMBER AND METHOD FOR
FABRICATING CAPACITOR BY USING
THE SAME
Attorney Docket Number:: 29926/39505
Request for Early Publication?:: No
Request for Non-Publication?:: No
Total Drawing Sheets:: 10
Small Entity?:: No
Petition included?:: No
Secrecy Order in Parent Appl.?:: No

Applicant Information

Applicant Authority Type:: Inventor
Primary Citizenship Country:: Korea, Republic of
Status:: Full Capacity
Given Name:: Young-Soo
Family Name:: Kim
City of Residence:: Kyoungki-do
Country of Residence:: Korea
Street of mailing address:: San 136-1, ami-Ri Bubal-Eub
Ichon-shi,



City of mailing address:: Kyoungki-do
Country of mailing address:: Korea, Republic of
Postal or Zip Code of mailing address:: 467-860

Correspondence Information

Correspondence Customer Number:: 04743

Representative Information

Representative Customer Number:: 04743

Foreign Priority Information

Country::	Application number::	FilingDate::	Priority Claimed::
Korea, Republic of	2002-42296	07/19/02	Yes

Assignee Information

Assignee name:: HYNIX SEMICONDUCTOR INC.
Street of mailing address:: San 136-1, Ami-Ri, Bubal-Eub, Ichon-Shi
City of mailing address:: Kyoungki-Do
Country of mailing address:: Korea, Republic of
Postal or Zip Code of mailing address:: 467-860